

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

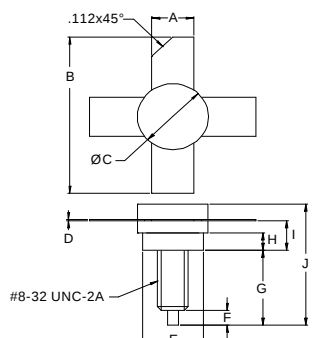
The **ASI VHB50-28S** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	6.5 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	75 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.3 °C/W

PACKAGE STYLE .380 4L STUD		
		
DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05
ORDER CODE: ASI10730		

CHARACTERISTICS $T_C = 25\text{ °C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 200\text{ mA}$			35			V
BV_{CES}	$I_C = 200\text{ mA}$			65			V
BV_{EBO}	$I_E = 10\text{ mA}$			4.0			V
I_{CBO}	$V_{CB} = 28\text{ V}$					2.0	mA
I_{CES}	$V_{CE} = 28\text{ V}$ $T_C = 125\text{ °C}$					10	mA
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 500\text{ mA}$		5.0		---	---
C_{ob}	$V_{CB} = 28\text{ V}$	$f = 1.0\text{ MHz}$				80	pF
f_T	$V_{CE} = 10\text{ V}$	$I_C = 500\text{ mA}$	$f = 100\text{ MHz}$	200			MHz
P_G	$V_{CE} = 28\text{ V}$	$P_{OUT} = 50\text{ W}$	$f = 150\text{ MHz}$	6.0			dB
η_C					60		%